

WAFER TESTING SYSTEMS AND ASSOCIATED METHODS OF USE AND MANUFACTURE

CROSS REFERENCE TO RELATED APPLICATION

[0001] This application claims priority to U.S. Provisional Application No. 61/404,234, filed on September 28, 2010, and entitled "ARRANGEMENT OR STACK OF A WAFER CHUCK, WAFER, WAFER TRANSLATOR, AND TESTER DIB BOARD WITH THREE INDEPENDENT VACUUM COMPARTMENTS TO APPLY AND MANAGE CONTACT PRESSURE WITHIN THE STACK; ADDITIONALLY A SYSTEM TO CREATE STANDARDIZED CONTACT PATTERNS ACROSS THE TESTER SIDE OF THE WAFER TRANSLATOR TO MINIMIZE LEAD TIME AND COST TO CREATE CUSTOM TRANSLATORS FOR SPECIFIC WAFER," which is incorporated herein in its entirety by reference.

TECHNICAL FIELD

[0002] The present technology relates generally to semiconductor manufacturing equipment, and more particularly, to systems and methods for maintaining a chuck, a wafer, a wafer translator, and an interposer in a releaseably attached state.

BACKGROUND

[0003] Semiconductors are used in digital cameras, cell phones, computers, and numerous other technology applications. Semiconductors are typically manufactured in batches individually containing a plurality of semiconductor wafers within and upon which dies having integrated circuits are formed through a variety of semiconductor manufacturing operations. Completed wafers are electrically tested to determine which dies on the wafer are capable of operating according to predetermined specifications. In this way, defective dies are not packaged or otherwise incorporated into finished products.

[0004] During electrical testing, conductive regions on the surface of the semiconductor wafer are commonly contacted with a probe card. The wafer is typically mounted on a moveable chuck, which is used to position the wafer relative

to a probe card, and to hold the wafer in place during testing. Conventional testing systems utilizing probe cards are expensive and cannot be miniaturized beyond a certain size. Accordingly, it would be desirable to have an improved wafer testing system that can be used to inexpensively, quickly, and effectively test individual dies on semiconductor wafers.

BRIEF DESCRIPTION OF THE DRAWINGS

[0005] Figure 1 is a schematic block diagram of a test environment configured in accordance with an embodiment of the presently disclosed technology.

[0006] Figure 2 is a partially schematic illustration of a wafer testing stack configured in accordance with an embodiment of the presently disclosed technology.

[0007] Figure 3A is a partially schematic isometric view of a wafer translator configured in accordance with an embodiment of the presently disclosed technology.

[0008] Figure 3B is a partially schematic cross-sectional side view of a wafer translator operably coupled to an interposer in accordance with an embodiment of the presently disclosed technology.

[0009] Figure 4A is a partially schematic isometric view of a wafer coupled to a wafer chuck in accordance with an embodiment of the presently disclosed technology.

[0010] Figure 4B is a partially schematic cross-sectional side view of a wafer and wafer chuck operably coupled to the wafer translator in accordance with an embodiment of the presently disclosed technology.

[0011] Figure 5 is a partially schematic side view of a portion of the wafer testing stack of Figure 2 during an attachment process in accordance with an embodiment of the presently disclosed technology.

[0012] Figure 6 is a partially schematic side view of the portion of the wafer testing stack of Figure 5 after the wafer chuck, wafer, wafer translator, and interposer have been releaseably attached in a stacked configuration.

DETAILED DESCRIPTION

[0013] Embodiments of the presently disclosed technology are directed generally to wafer testing systems and associated methods of use and manufacture. Reference herein to "one embodiment", "an embodiment", or similar formulations, means that a particular feature, structure, operation, or characteristic described in connection with the embodiment, is included in at least one embodiment of the present technology. Thus, the appearances of such phrases or formulations herein are not necessarily all referring to the same embodiment. Furthermore, various particular features, structures, operations, or characteristics may be combined in any suitable manner in one or more embodiments.

[0014] The terms "pad," "contacts," and "electrical terminal," as used herein, generally refer to a conductive region where physical and electrical connection between one component and another is made. In the context of integrated circuits, "pad" typically refers to a metallized region at or near the surface of the integrated circuit, which is commonly used to form a physical connection terminal for communicating signals to and/or from the integrated circuit. Such integrated circuit pads may be formed of a metal, a metal alloy, or a stack structure including several layers of metals and/or metal alloys that are present, typically, at the uppermost layer of conductive material of an integrated circuit.

[0015] The expression "wafer translator" refers to an apparatus facilitating the connection of I/O pads (sometimes referred to as terminals, pads, contact pads, bond pads, chip pads, or test pads) of unsingulated integrated circuits, to other electrical components. It will be appreciated that "I/O pads" is a general term, and that the present technology is not limited with regard to whether a particular pad of an integrated circuit is part of an input, output, or input/output circuit.

[0016] A wafer translator may be disposed between a wafer and other electrical components. The wafer translator can include a substrate having two major surfaces, each surface having terminals disposed thereon, and electrical pathways disposed through the substrate to provide for electrical continuity between at least one terminal on a first surface and at least one terminal on a second surface. The major surface designed to be disposed toward a wafer can be referred to as the wafer-side of the wafer translator. The wafer-side of the wafer translator can have a

pattern of terminals that matches the layout of at least a portion of the I/O pads of the integrated circuits on the wafer. The wafer translator, when disposed between a wafer and other electrical components, makes electrical contact with one or more I/O pads of a plurality of integrated circuits on the wafer, providing an electrical pathway therethrough to the other electrical components.

[0017] The wafer translator is a structure that can be used to achieve electrical connections between one or more electrical terminals that have been fabricated at a first scale, or dimension, and a corresponding set of electrical terminals that have been fabricated at a second scale, or dimension. The wafer translator can provide an electrical bridge between the smallest features in one technology (e.g., pins of a probe card) and the largest features in another technology (e.g., bonding pads of an integrated circuit). For convenience, a wafer translator can be referred to simply as translator where there is no ambiguity as to its intended meaning.

[0018] The expression "translated wafer" refers to a wafer/wafer translator pair that are in the attached state, and a predetermined portion of, or all of, the contact pads of the integrated circuits on the wafer are in electrical contact with corresponding electrical connections disposed on the wafer-side of the translator. Removable attachment may be achieved, for example, via a vacuum, or other pressure differential attachment. That is, by reducing the pressure in the space between the wafer and the wafer translator relative to the pressure (typically atmospheric pressure) outside that space, the wafer and wafer translator are placed in the attached state.

[0019] The term "tester" as used herein refers to equipment, typically electrical equipment, which is used to determine whether an integrated circuit is performing in accordance with a predetermined specification. The terms "chip," "integrated circuit," "semiconductor device," and "microelectronic device" are sometimes used interchangeably in this field. The present technology relates to the manufacture and test of chips, integrated circuits, semiconductor devices and microelectronic devices as these terms are commonly understood in the field.

[0020] Described below are several embodiments of wafer testing systems and associated methods of use and manufacture. In one embodiment the wafer testing system includes an assembly for releaseably attaching a wafer to a wafer translator

and the wafer translator to an interposer by means of separately operable vacuums, or pressure differentials. The assembly can include a wafer translator support ring coupled to the wafer translator, wherein a first flexible material extends from the wafer translator support ring so as to enclose the space between the wafer translator and the interposer so that the space may be evacuated by a first vacuum through one or more first evacuation paths. The assembly can further include a wafer support ring coupled to the wafer and the chuck, wherein a second flexible material extends from the wafer support ring so as to enclose the space between the wafer and the wafer translator so that the space may be evacuated by a second vacuum through one or more second evacuation pathways.

[0021] In another aspect of the present technology, the use of a wafer/wafer translator/interposer in the attached state provides the electrical connection to pads of unsingulated integrated circuits on the wafer in such a manner that the pads are substantially undamaged in the process of making these electrical connections. Various embodiments of the present technology provide a sealing arrangement for facilitating the vacuum attachment of the wafer/wafer translator pair and/or the wafer translator/interposer pair. All or some portion of the air, or any gas or combination of gases, is evacuated from between the wafer and wafer translator through one or more evacuation pathways.

[0022] Figure 1 is a schematic block diagram of a test environment 100 in accordance with an embodiment of the present technology. In the example of Figure 1, the test environment 100 includes a tester 102 and a prober 110. The tester 102 is electrically coupled to the prober 110 via a cable 104. The prober 110 can include a Device Interface Board ("DIB") 120, an interposer 130, and a wafer translator 140. As will be discussed in further detail below, the wafer translator 140 provides a removable electrical connection to a wafer 150. The wafer 150 includes a plurality semiconductor dies, each die having one or more contacts. The wafer 150 is supported by a probe chuck 160.

[0023] During a representative wafer test, the wafer translator 140 and the wafer 150 are positioned such that one or more probes on the wafer translator 140 contact bond pads on the wafer 150. This allows the tester 102 to send stimulus signals to the wafer 150 via a path that includes the cable 104, the DIB 120, the interposer 130, and the wafer translator 140. Similarly, the tester 102 may receive

response signals from the wafer 150 over the same path. For example, the tester 102 can obtain diagnostics from individual pads (e.g., the tester 102 can supply a signal to a pad and analyze response at the same pad or a different pad).

[0024] Figure 2 is a partially schematic illustration of a wafer testing stack 270 in accordance with an embodiment of the present technology. The testing stack 270 includes several of the features discussed above with reference to Figure 1, including the DIB 120, the interposer 130, the wafer translator 140, the wafer 150, and the chuck 160. The testing stack 270 illustrates these features in an attached arrangement, such that a tester (e.g., the tester 102 in Figure 1) can be operably connected to the wafer 150 via an electrical bridge, link, or path running through the DIB 120, the interposer 130, and the wafer translator 140.

[0025] The DIB 120 can be a printed circuit board including a substrate 227 having a first surface 222 and a second surface 224 opposite the first surface 222. One or more cable connectors 206 can be coupled to the first surface 222. The cable connectors 206 can be configured to operably interface with a cable or tester (such as the cable 104 and the tester 102 shown in Figure 1). One or more DIB contacts 228 can be disposed on the second surface 224 of the DIB 120. The contacts 228 can be operably connected to the cable connectors 206 via electrical pathways 226 running through the substrate 227.

[0026] The interposer 130 can be a multi-layer printed circuit board, including an interposer substrate 237 having a first surface 232 facing the second surface 224 of the DIB 120 and a second surface 234 opposite the first surface 232. The interposer 130 can include one or more contact pins 236 positioned in vias 235 in the interposer substrate 237. The vias 235 can traverse the interposer substrate 237 from the first surface 232 to the second surface 234. The contact pins 236 can be operably coupled to contact pads 238 at or near the first surface 232 of the interposer. The contact pads 238 can have a larger surface area than the contact pins 236 and can accordingly improve electrical connection with the DIB contacts 228. The contact pins 236 and contact pads 238 can be made of conductive material, such as nickel/gold. In the illustrated embodiment, the contact pins 236 extend beyond the second surface 234 of the interposer 130 toward the wafer-translator 140. In other embodiments, the contact pins 236 may vary in height relative to the second surface 234 of the interposer 130 and/or relative to other individual contact pins 236.

[0027] The wafer translator 140 can include a substrate 247 having a first surface 242 facing the interposer 130. First electrical terminals 248 are located at or near the first surface 242 and are configured to interface with the interposer contact pins 236. Second electrical terminals 249 are located at or near a second surface 244 of the wafer translator 140 opposite the first surface 242 to interface with bond pads 258 on a first surface 252 of the wafer 150. Electrical pathways 246 disposed in vias 245 that traverse the wafer translator substrate 247 provide for electrical continuity between at least one electrical terminal 248 at the first surface 242 and at least one electrical terminal 249 at the second surface 244. The wafer translator 140 accordingly provides an electrical bridge, link or path between the pins 236 on the interposer 130 and bond pads 258 on the wafer 150. The bond pads 258 achieve the final electrical connection between the tester and the internal circuitry of the wafer 150.

[0028] The pattern of electrical terminals 249 at the second surface 244 of the wafer translator 140 can match or correspond to the layout of at least a portion of the pads 258 on the wafer 150. The wafer 150 and/or wafer translator 140 can have different patterns or arrangements of pads 258 and electrical terminals 249 in various embodiments of the technology. For example, in certain embodiments, the bond pads 258 and translator electrical terminals 249 are arranged in a polygonal (e.g., hexagonal), or honeycomb-type matrix. An advantage of the hexagonal arrangement is that it facilitates close-packing for the terminals and bond pads. In further embodiments, the bond pads 258 are arranged in a grid. The electrical terminals 249 can be at least partially made of nickel, platinum, nickel-platinum or other electrically-conductive materials and the bond pads 258 can be at least partially made of aluminum or other electrically-conductive material. In certain embodiments, the electrical terminals 249 can be made of a material harder than that of the bond pads 258. The electrical terminals 249 can be deposited or formed on the wafer translator 140 by physical or chemical vapor deposition, screen printing, or other methods.

[0029] In some embodiments, the wafer-translator 140 can be generally the same size and/or shape as the wafer 150 and can include a sufficient quantity of electrical terminals 249 to contact and test all of the pads 258 on the wafer 150 with a single touch (e.g., a single instance of contacting the translator 140 with the wafer

150). In certain embodiments, the electrical terminals 249 of the wafer-translator 140 contact 130,000 or more pads 258 on the wafer 150 in a single touch. In a particular embodiment, one million or more pads 258 on the wafer 150 are contacted by a single touch of the wafer translator 140. In certain embodiments, the wafer translator 140 has a different size and/or shape relative to the wafer 150 and tests only a portion of the pads 258 on the wafer 150 at a time. In this latter arrangement, the wafer testing can be performed by tiling the tester across multiple portions of the wafer 150 in succession. For example, in a particular embodiment, two regions of the wafer having 40,000 pads 258 each are contacted in succession by the wafer translator 140.

[0030] The structure of the wafer 150 and/or the wafer translator 140 can be tailored to improve contact between these components. For example, the stiffness of the wafer translator 140 can be varied in various embodiments of the technology in order to reduce the need for the pads 258 and electrical terminals 249 to comply with one another. In certain embodiments, a flexible wafer translator 140 offers compliance to the surface of a wafer 150 mounted on a rigid support, while in other embodiments the wafer translator 150 is more rigid. In certain embodiments, the wafer-translator 140 includes one or more stiffener boards or other stiffening features. In particular embodiments, the wafer translator 140 is at least partially made of silicon or ceramic and the wafer is at least partially made of silicon.

[0031] Contact between the wafer 150 and the wafer translator 140 can be further improved by reducing bending/cantilevering at the edges of the wafer 150 by adding dummy mechanical contacts or other elevations toward the edges of the wafer 150. Furthermore, the height of pads 258 and/or electrical terminals 249 can be varied either statically or dynamically (e.g., by spring or similar force) across the wafer 150 and/or the wafer translator 140 to improve electrical contact.

[0032] In certain embodiments, the wafer translator 140 is removeably or fixedly coupled to a translator support ring 280. The translator support ring 280 can include one or more seals 284 extending therefrom. The seals 284 can be configured to provide an airtight or generally airtight seal between the wafer translator 140 and the interposer 130. The translator support ring 280 can include one or more evacuation pathways, or ports, 282 that traverse the support ring 280. In some embodiments, the evacuation pathways 282 can be fitted with valves to open and close the

evacuation pathways 282. As will be discussed in further detail below with reference to Figures 3A, 3B, and 5, a first vacuum can be drawn on a space 286 between the interposer 130 and the wafer translator 140 to evacuate air via the evacuation pathways 282, thereby creating a pressure differential that can pull together and releaseably attach the interposer 130 and wafer translator 140. In certain embodiments, the translator support ring 280 has a diameter less than the diameter of the interposer 130 so that the translator support ring evacuation pathway 282 is inside the circumference of the interposer 130. In further embodiments, the translator support ring 290 has a diameter that is the same as or greater than the diameter of the interposer 130, and the evacuation pathways 282 can be in the same or different locations relative to the interposer 130.

[0033] The wafer 150 can be positioned in or on a chuck support ring 290 that peripherally surrounds, or at least partially surrounds, the wafer 150 in a manner similar to that described above with reference to the translator support ring 280. The chuck support ring 290 can be integral with the chuck 160 or can comprise a separate component. The chuck support ring 290 can include one or more seals 294 extending therefrom. The seals 294 can be configured to provide an airtight or generally airtight seal between the wafer 150 and the wafer translator 140. The chuck support ring 290 can include one or more evacuation pathways, or ports, 292 that access a space 296 between the wafer translator 140 and the wafer 150. For example, the ports 292 can traverse the chuck 160 from a first surface 262 of the chuck 160 to a second surface 264 of the chuck opposite the first surface 262. In certain embodiments, the evacuation pathways 292 can be fitted with valves to open and close the evacuation pathways 292. As will be discussed in further detail below with reference to Figures 4A, 4B, and 5, a second vacuum can operate in the space 296 between the wafer translator 140 and the wafer 150, thereby creating a pressure differential that pulls together and releaseably attaches the wafer translator 140 and the wafer 150. In some embodiments, air or other gas can be evacuated from the air space 296 via the evacuation pathways 292. It will be appreciated that that other suitable configurations for coupling the evacuation pathways 292 to a vacuum source may be used in other embodiments. In certain embodiments, the wafer 150 and the wafer translator 140 can be removeably attached by systems and methods described in U.S. Patent Application No. 12/547,418, assigned to the assignee of the

present application, filed on August 25, 2009, and entitled "MAINTAINING A WAFER/WAFER TRANSLATOR PAIR IN AN ATTACHED STATE FREE OF A GASKET DISPOSED THEREBETWEEN," which is hereby incorporated by reference in its entirety.

[0034] In some embodiments, the wafer 150 can be releaseably coupled to the chuck 160 with a third vacuum. The wafer 150 can be pulled toward and removeably held down on the chuck 160, with a second surface 254 of the wafer 150 contacting the first surface 262 of the chuck 160. The chuck 160 can include vacuum holes 298 to effect the suction between the chuck 160 and the wafer 150. In a particular embodiment, the chuck has a diameter of about 317 mm and the wafer has a diameter of about 300 mm. In other embodiments, the chuck and/or wafer can have other dimensions. In certain embodiments, the chuck support ring 290 has a diameter less than the diameter of the translator support ring 280 so that the translator support ring evacuation pathway 282 is outside the circumference of the chuck support ring 290. In further embodiments, the chuck support ring 290 has the same or a greater diameter than the translator support ring 280. The wafer 150 can be delivered into the chuck 160 by a wafer robot or similarly well-known wafer transport equipment. In some embodiments, the chuck 160 can include a plurality of lift pins to support the second surface 254 of the wafer 150.

[0035] Figure 3A is a partially schematic isometric view of a wafer translator configured 140 in accordance with an embodiment of the present technology. Figure 3B is a partially schematic cross-sectional side view of the wafer translator 140 operably coupled to the interposer 130 in accordance with an embodiment of the present technology. Referring first to Figure 3A, the wafer translator 140 is coupled to and circumferentially surrounded by the translator support ring 280. In certain embodiments, the support ring 280 is fabricated from a metal, but can include other materials in other embodiments. The support ring 280 includes a groove 385 configured to receive the seal 284. In various embodiments, the seal 284 can be more or less rigid. In the illustrated example, the groove 385 runs continuously around the first surface 242 of the support ring 280. The support ring 280 can include one or more evacuation pathways circumferentially inward of the groove 385. As described above with reference to Figure 2, the evacuation pathways can

traverse through the translator support ring 280 and can be fitted with valves to open and close the evacuation pathways.

[0036] Referring now to Figure 3B, the seal 284 includes a base portion 387 seated in the groove 385 and an upper portion 389 extending outwardly from the support ring 280. The groove 385 can be flanged so as to retain the base portion 387 of the seal 284. In the illustrated embodiment, the upper portion 389 is angled circumferentially outward with respect to the top side of the support ring 280, but in other embodiments the upper portion 389 can be vertical or approximately vertical relative to the top side of the support ring 280. The upper portion 389 is configured to act as a seal to maintain a vacuum or partial vacuum in the space 286 between the wafer translator 140 and the interposer 130. The vacuum holds the wafer translator 140 and interposer 130 in a removeably attached state. The wafer translator 140 and the interposer 130 can be released from one another by releasing the seal 284 or by opening a valve to open the evacuation pathways.

[0037] Figure 4A is a partially schematic isometric view of the wafer 150 positioned on the wafer chuck 160 in accordance with an embodiment of the present technology. Figure 4B is a partially schematic cross-sectional side view of the wafer 150 and wafer chuck 160 operably coupled to the wafer translator 140 in accordance with an embodiment of the present technology. Referring first to Figure 4A, the wafer 150 is coupled to and circumferentially surrounded by the chuck support ring 290. The chuck support ring 290 includes a groove 495 configured to receive the seal 294. In the illustrated embodiment, the groove 495 runs continuously around the topside of the support ring 290. The chuck support ring 290 can include one or more evacuation pathways (not visible in Figure 4A) circumferentially inward of the groove 495. The evacuation pathways can traverse from the first surface 262 of the chuck to the second surface 264. The evacuation pathways in the ring 290 may be fitted with valves to open and close the evacuation pathways. In some embodiments, the chuck support ring 290 is integral to the chuck 160, and the chuck 160 is releaseably coupled to the wafer 150 (e.g., the chuck 160 can act as a vacuum hold-down device for the wafer 150 via the chuck vacuum holes 298).

[0038] Referring now to Figure 4B, the seal 294 includes a base portion 497 seated in the groove 495 and an upper portion 499 extending outwardly from the support ring 290. The groove 495 can be flanged so as to retain the base portion

497 of the seal 294. In the illustrated embodiment, the upper portion 499 is angled with respect to the top side of the support ring 290, but in other embodiments the upper portion 499 can be vertical or approximately vertical. The upper portion 499 is configured to act as a seal to maintain a vacuum or partial vacuum in the space 296 between the wafer translator 140 and the wafer 150. The vacuum holds the wafer translator 140 and wafer 150 in a removeably attached state. The wafer translator 140 and wafer 150 can be released from one another by releasing the seal 294 or by opening a valve to open one or more evacuation pathways.

[0039] Figure 5 is a partially schematic side view of a portion of the wafer testing stack 270 of Figure 2 during an attachment process in accordance with an embodiment of the present technology. As described above with reference to Figures 2-4B, a plurality of vacuums can independently operate to (a) removeably attach the interposer 130 to the wafer translator 140, (b) removeably attach the wafer translator 140 to the wafer 150, and/or (c) removeably attach the wafer 150 to the chuck 160. In the illustrated embodiment, the chuck 160 and wafer 150 are removeably attached and together move upward toward the wafer translator 140 while the interposer 130 moves downward toward the wafer translator 140. In certain embodiments, only one of the interposer 130 and the chuck 160 moves toward the other while one of these elements remains stationary. Typically, the wafer translator 140 and wafer 150 are aligned with respect to each other such that electrical terminals 249 disposed at the second surface 244 of the wafer translator 140 and pads 258 at the first surface 252 of the wafer 150 make electrical contact with each other when the space 296 between the wafer 150 and wafer translator 140 is evacuated. The interposer 130 and wafer translator 140 are likewise aligned with respect to each other such that the electrical terminals 248 disposed on the first surface 242 of the wafer translator 140 and the interposer contact pins 236 make electrical contact with each other when the space 286 between the wafer translator 130 and the interposer 130 is evacuated.

[0040] As the wafer 150 approaches the wafer translator 140, the chuck seal 294 contacts the second surface 244 of the wafer translator 140 or the wafer translator support ring 280 and seals the space 296 between the wafer 150 and the wafer translator 140. As the air or other gas is drawn out through the chuck support ring evacuation pathways 292 via a vacuum, the air pressure of the atmosphere

presses wafer translator 140 and wafer 150 into a removeably attached state wherein the electrical terminals 249 on the second surface 244 of the wafer translator 140 make electrical contact with the pads 258 of the first side 252 of the wafer 150. Likewise, as the interposer 130 approaches the wafer translator 140, the wafer translator seal 284 contacts a peripheral annular portion of the second surface 234 of the interposer 130 and seals the space 286 between the interposer 130 and the wafer translator 140. Air or other gas between the wafer translator 140 and the interposer 130 is drawn out from the space 286 through evacuation pathways 282. The air pressure outside the wafer translator 140 and the interposer 130 can press these components into a removeably attached state wherein the electrical terminals 248 on the first side 242 of the wafer translator 140 make electrical contact with the contact pins 236 on the second side 234 of the interposer 130. While the illustrated embodiment shows the interposer 130, wafer translator 140, and wafer 150/chuck 160 simultaneously attaching to form a wafer testing stack, in certain embodiments the components may attach to one another sequentially (e.g., the interposer 130 and wafer translator 140 may attach to one another before the wafer translator 140 is attached to the wafer 150).

[0041] Figure 6 is a partially schematic side view of the portion of the wafer testing stack 270 of Figure 5 after the chuck 160, wafer 150, wafer translator 140, and interposer 130 have been releaseably attached in a stacked configuration. The seal 284 extending from the wafer translator support ring 280 engages the interposer 130 to create an airtight or generally airtight seal between the interposer 130 and the wafer translator 140 after these components have been pulled together via a first vacuum. The seal 294 extending from the chuck support ring 290 likewise creates a second airtight or generally airtight seal between the wafer 150 and the wafer translator 140 after these components have been pulled together via a second vacuum. The chuck 160 and wafer 150 have been releaseably attached via a third vacuum operating through chuck vacuum holes 298.

[0042] The first, second, and third vacuums can be independently operable, providing different pressure forces between the chuck 160 and wafer 150, between the wafer 150 and wafer translator 140, and between the wafer translator 140 and the interposer 130. The pressure forces between these components can accordingly be independently altered to improve contact and testing performance without

excessive pressure force that can damage the contacts or other components of the devices. In further embodiments, the air space between two or more of the components can be in fluid communication with one another, and can be sealed by a common vacuum.

[0043] Embodiments of the present technology can provide many advantages in the wafer testing technologies. For example, the wafer testing systems disclosed herein can be easily adaptable when it is necessary to change out types of wafers for testing. More specifically, when a new type of wafer, having an alternate arrangement of pads, is ready to be tested, only the wafer translator (or only the wafer-side of the wafer-translator) needs to be replaced to match the bond pad arrangement of the new wafer. The DIB and interposer can universally accommodate multiple types of wafers. This arrangement can lead to substantial cost savings over traditional systems in which the entire prober are replaced when a wafer having a new configuration was used.

[0044] The ability to accommodate different types of wafers is additionally supported by the separately-controllable vacuums. More specifically, the vacuums can control the pressure forces between components to provide for effective electrical contact, and can adjust the pressure differential between the wafer and the wafer translator to suit the specific arrangement and number of bond pads on the new wafer. The multi-vacuum system also enables the wafer-translator to fine-tune contact forces and more effectively contact the entire wafer, thereby testing all of the pads on the wafer with a single touch. This can reduce testing time and can reduce wear on individual pads from repeated or overly-forceful testing.

[0045] Furthermore, the systems disclosed herein provide for a wafer translator having contacts that are smaller than those in typical testing systems. The smaller contacts on the translator can increase the testing rate of the wafer because there is less of an antenna effect between smaller contacts. In certain embodiments, the testing rate can be about 500 Mbits per second. In further embodiments the testing rate can be about 120 Gbits per second.

[0046] From the foregoing, it will be appreciated that specific embodiments of the technology have been described herein for purposes of illustration, but that various modifications may be made without deviating from the scope of the

technology. For example, the wafers and translators can have contacts arranged in configurations other than those expressly shown and described above. Certain aspects of the disclosure described in the context of particular embodiments may be combined or eliminated in other embodiments. For example, some embodiments include only particular elements of the wafer stack. Accordingly, the present disclosure and associated technology can encompass other embodiments not expressly shown or described herein.

CLAIMS

I/We claim:

1. A wafer testing system, comprising:
a tester;
a prober;
a cable between the tester and the prober, wherein the prober includes:
an interposer;
a wafer translator proximate the interposer; and
a translator support configured to receive the wafer translator, the translator support having a seal configured to at least partially hermetically seal a space between the wafer translator and the interposer.
2. The wafer testing system of claim 1 wherein:
the interposer includes a contact pin proximate the wafer translator;
the wafer translator includes a first terminal at a first side proximate the interposer, a second terminal at a second side, and an electrical pathway between the first and second terminals; and
the contact pin is configured to contact the first terminal when the space is at least partially under vacuum.
3. The wafer testing system of claim 1 wherein the translator support includes a pathway configured to pass a gas to/from the space between the wafer translator and the interposer.
4. The wafer testing system of claim 1 wherein:
the translator support includes a ring having a groove configured to receive the seal; and
the seal includes a generally flexible material at least partially received in the groove of the ring.

5. The wafer testing system of claim 1 wherein:
the translator support includes a ring having a groove; and
the seal includes a base portion and an upper portion extending from the base portion, the base portion being received in the groove of the ring.
6. The wafer testing system of claim 1 wherein:
the translator support includes a ring having a groove with a flange;
the seal includes a base portion and an upper portion extending from the base portion; and
the base portion is received in the groove of the ring and retained by the flange of the groove.
7. The wafer testing system of claim 1 wherein:
the translator support includes a ring having a groove with a flange;
the seal includes a base portion and an upper portion extending from the base portion;
the base portion is received in the groove of the ring and retained by the flange of the groove; and
the upper portion is angled circumferentially outward with respect to the translator support.
8. The wafer testing system of claim 1 wherein:
the seal is a first seal;
the wafer testing system further includes:
a chuck configured to hold a wafer proximate to the second side of the wafer translator;
a chuck support configured to receive the chuck, the chuck support having a second seal configured to at least partially hermetically seal a space between the wafer and the wafer translator.
9. A wafer translator, comprising:
a substrate having a first side and a second side;
a first terminal at the first side;

a second terminal at the second side opposite the first side;
and an electrical pathway between the first and second terminals; and
a translator support configured to receive the substrate, the translator support
having a seal configured to at least partially hermetically seal a space
between the wafer translator and an interposer proximate the first side
of the wafer translator.

10. The wafer translator of claim 9 wherein the translator support includes
a pathway configured to pass a gas to/from the space between the wafer translator
and the interposer.

11. The wafer translator of claim 9 wherein:
the translator support includes a ring having a groove configured to receive
the seal; and
the seal includes a generally flexible material at least partially received in the
groove of the ring.

12. The wafer translator of claim 9 wherein:
the translator support includes a ring having a groove; and
the seal includes a base portion and an upper portion extending from the base
portion, the base portion being received in the groove of the ring.

13. The wafer translator of claim 9 wherein:
the translator support includes a ring having a groove with a flange;
the seal includes a base portion and an upper portion extending from the base
portion; and
the base portion is received in the groove of the ring and retained by the
flange of the groove.

14. The wafer translator of claim 9 wherein:
the translator support includes a ring having a groove with a flange;
the seal includes a base portion and an upper portion extending from the base
portion;

the base portion is received in the groove of the ring and retained by the flange of the groove; and
the upper portion is angled circumferentially outward with respect to the translator support.

15. A method for establishing contact with a wafer having a bond pad, comprising:
placing an interposer and a wafer translator proximate the wafer, the wafer translator having a terminal facing the bond pad of the wafer;
at least partially hermetically sealing a first space between the interposer and the wafer translator and a second space between the wafer and the wafer translator;
establishing a first vacuum in the first space and a second vacuum in the second space; and
contacting the terminal of the wafer translator with the bond pad of the wafer with the first and second vacuums.
16. The method of claim 15, further comprising adjusting at least one of the first and second vacuums based on a target degree of contact between the terminal and the bond pad.
17. The method of claim 15, further comprising adjusting at least one of the first and second vacuums such that the terminal and the bond pad are in electrical and physical contact with each other.
18. The method of claim 15, further comprising:
holding the wafer on a chuck, the wafer having a first side facing the wafer translator and a second side facing the chuck;
establishing a third vacuum between the second side of the wafer and the chuck; and
adjusting at least one of the first, second, and third vacuums based on a target degree of contact between the terminal and the bond pad.

19. The method of claim 15 wherein:
the bond pad is a first bond pad;
the terminal is a first terminal;
the wafer also includes a plurality of additional bond pads;
the wafer translator also includes a plurality of additional terminals corresponding to the bond pads of the wafer; and
the method further includes adjusting at least one of the first and second vacuums based on a target degree of contact between the plurality of terminals and the corresponding bond pads.

20. The method of claim 15, further comprising controlling forces on the wafer translator by controlling at least one of a first pressure in the first space and a second pressure in the second space to be different than the other.

21. An apparatus for establishing contact with a wafer having a bond pad, comprising:
an interposer;
a wafer translator having a first side proximate the interposer and a second side proximate the wafer, the wafer translator having a terminal facing the bond pad of the wafer;
means for at least partially hermetically sealing a first space between the interposer and the wafer translator; and
means for at least partially hermetically sealing a second space between the wafer and the wafer translator.

22. The apparatus of claim 21, further comprising:
means for establishing a first vacuum in the first space;
means for establishing a second vacuum in the second space.

23. The apparatus of claim 21, further comprising:
means for establishing a first vacuum in the first space;
means for establishing a second vacuum in the second space; and

means for adjusting at least one of the first and second vacuums based on a target degree of contact between the terminal and the bond pad.

24. The apparatus of claim 21 wherein the means for adjusting is configured to adjust at least one of the first and second vacuums to be different from the other.